

Dynamic Simulation of High Brightness Semiconductor Lasers

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Outline

Modelling

Numerical Solution

•Results

•Summary

Mathematical Modelling and Numerical Simulation

•Semiconductor lasers are characterized by a huge amount of physical and geometrical parameters

Time-space instabilities like
Pulsations
Self-focusing
Filamentation
Thermal Lensing

Restrictions to beam quality and wavelength stability.

 Mathematical modeling and computer simulations are needed for —preparing technological processes to choose optimal parameters —understanding experimental data —predicting new laser designs.



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Model for β

Effective refractive index depends on carrier density N and temperature. We use the following model for β :

$$\beta = \delta_0(x,z) + \delta_{\Sigma}(x,z,N,J) + i \frac{g(x,z,N,u) - \alpha(x,z)}{2},$$

$$\delta_{\Sigma}(x,z,N,J) = \delta_n(x,z,N) + \delta_T(x,z,J),$$

where

- δ_0 index variation in space,
- $\delta_n = -\sqrt{n'N}$ dependence of effective index on the carrier density,
- δ_T temperature dependence of effective index,
- $g(x, z, N, u) = g'(x, z) \frac{\ln \frac{N(x, z, t)}{N_{tr}}}{1 + \epsilon ||u||^2}$ optical gain,
- $\alpha = \alpha(x, z)$ optical losses.
- Model parameters determined at FBH and HU Berlin experimentally.

Model Equations

$$\frac{1}{v_g}\partial_t u^{\pm} = \frac{-i}{2k_0\bar{n}}\partial_{xx}u^{\pm} + (\mp\partial_z - i\beta)u^{\pm} - i\kappa u^{\mp} - \frac{\bar{g}}{2}\left(u^{\pm} - p^{\pm}\right)$$
$$\partial_t p^{\pm} = \bar{\gamma}\left(u^{\pm} - p^{\pm}\right) + i\bar{\omega}p^{\pm}$$
$$\partial_t n = d_n\partial_{xx}n + \frac{J}{qd} - R(n) - v_g \Re \epsilon \langle u, g(n, u)u - \bar{g}(u-p) \rangle_{\mathbb{C}^2}$$

$$u^+(t,0,x) = r_0(x)u^-(t,0,x) + \alpha(t,x), \ u^-(t,l,x) = r_l(x)u^+(t,l,x).$$

- •Spont. Recombination $R(n) = A(x,z)n + B(x,z)n^2 + C(x,z)n^3$
- •Electrical injection J = J(t, z, x), optical injection $\alpha(t, x)$
- •Reflection coefficients $r_0(x)$, $r_l(x)$
- •All coefficients with the exception of k_0 , v_g , \bar{n} are spatially, i.e. laterally and longitudinally in (z, x) plane, nonhomogeneous and discontinuous (depending on the heterostructural lasergeometry)

Heating

Considered parametrically via Injection J(t, z, x):

$$I_{MO} = \int_{MO} J(x,z) dx dz, \ I_{PA} = \int_{PA} J(x,z) dx dz.$$

Nonlocal dependence via:

$$\delta_T(x,z) = \frac{k_0 n_g}{\lambda_0} \int c_T(x,z,\tilde{x},\tilde{z}) J(\tilde{x},\tilde{z}) d\tilde{x} d\tilde{z},$$

Shift of gain peak:

$$\overline{\lambda}(x,z) = \overline{\lambda}_0(x,z) + \int \nu_T(x,z,\tilde{x},\tilde{z}) J(\tilde{x},\tilde{z}) d\tilde{x} d\tilde{z}.$$

Spectral method

$$\frac{1}{v_g} \partial_t E^{\pm} = \frac{1}{2K} i \partial_{xx} E^{\pm} + (\mp \partial_z - i\beta(n)) E^{\pm} - i\kappa E^{\mp} - \frac{\overline{g}}{2} \left(E^{\pm} - P^{\pm} \right)$$
$$\partial_t P^{\pm} = \overline{\gamma} \left(E^{\pm} - P^{\pm} \right) + i\overline{\omega} P^{\pm}$$
$$\partial_t n = \frac{d_n \partial_{xx} n}{d_n + I(t) - R(n) - v_g \Re \epsilon \langle E, g(n)E - \overline{g}(E - P) \rangle_{\mathbb{C}^2}$$

•Step 1: Solve diffraction und diffusion (red coloring) with fast Fourier transform

Step 2: Solve remaining 1d hyperbolic system for each lateral x coordinate via integration along characteristics for fields
Solve fast P equation using exact solution formula with forward value for fields

•For spectral split method good L² convergence has been proven for smooth scalar nonlinear Schrödinger equation

•Use predictor / corrector method for optical nonlinearities

MOPA



Large Scale Problem

•Longitudinal discretization 5µm for 973nm laser

- •Time step 0.061ps
- •Lateral discretization 0.625µm
- •Resulting # of spatial variables:
 - •2.88 million (4mm long MOPA)
 - •8 16mm laser: 5.76 11.52 million variables
- •1d parameter scan of different dynamical regimes requires ≈300ns
- •2d scans 10-100 times more expensive

Parallel computing required!

Remark:

In comparison with previous 1d TWE model (*LDSL-tool*) calculation for HHI lasers our problem is 6400 times more complex!

10 × 300ns 2d parameter simulation on Euler cluster using multilayer parallel computing with MPI via Infiniband and POSIX Multithreading:

Single PC: 2415 hours, 100 days
Euler 1 node (2 quad Xeons, 8 cores): 833 hours, 34 days
Euler 4 nodes (32 cores): 288 hours, 9 days
Euler 9 nodes (72 cores): 114 hours, 4.75 days
Euler 3×9 nodes (216 cores): 38 hours, < 2 days
total number of available nodes on Euler: 32 (256 cores)

•A single low resolution 2d parameter scan of dynamical regimes requires about 1 day on whole cluster.

Results



Intensity and Carrier Distributions



Lateral Intensity Profiles



P-I Characteristics

Experiment:



Theory:

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Comparison with feedback experiments





- laser + external mirror form compound cavity laser
- coherent interference effects between reflected light and field inside the laser diode
- $I^{\uparrow} \Longrightarrow \lambda^{\uparrow} \Longrightarrow$ feedback phase changes \Longrightarrow intensity undulations
 - Feedback from taper into DFB-laser !

More recent for AFL: S. Bauer et al., Phys. Rev. E 69 (2004) 016206 O.Ushakov et al., Phys. Rev. Lett. 95 (2005) 123903

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Optical Spectra vs I_{PA}:

Experiment:

Simulation:



I_{MO}=350mA

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Optical Spectra vs I_{MO}:

Experiment:

Simulation:



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Wavelength Shift



Experiment

Simulation

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WIA

•Effective mathematical Model for MOPA's

•Heating effects parametrically included

•Detailed Comparison Experiment - Simulation

•Qualitative (longitudinal) understanding

Thank you for your Attention!